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6. AUTHORS Jackie Y. Ying Martin L. Panchula				
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) Department of Chemical Engineering Massachusetts Institute of Technology 77 Massachusetts Avenue, Room 66-544 Cambridge, MA 02139-4307		8. PERFORMING ORGANIZATION REPORT NUMBER		
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13. ABSTRACT (Maximum 200 words) This report describes preliminary results obtained from nitridation of nanocrystalline aluminum into nanocrystalline aluminum nitride. In comparison to commercial microcrystalline aluminum, the nanocrystalline aluminum displays significantly higher nitridation rates and does not require high temperatures to achieve significant conversion. Future research will examine the kinetics of the nitridation process and synthesizing nanocrystalline aluminum nitride directly in the forced flow reactor.				
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## "Nanocrystalline Processing and Interface Engineering of Si<sub>3</sub>N<sub>4</sub>-based Nanocomposites"

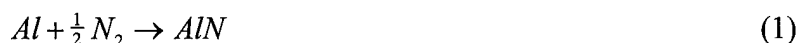
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Jackie Y. Ying  
Department of Chemical Engineering  
Massachusetts Institute of Technology  
Room 66-544, 77 Massachusetts Avenue  
Cambridge, MA 02139-4307  
Tel: (617) 253-2899  
Fax: (617) 258-5766

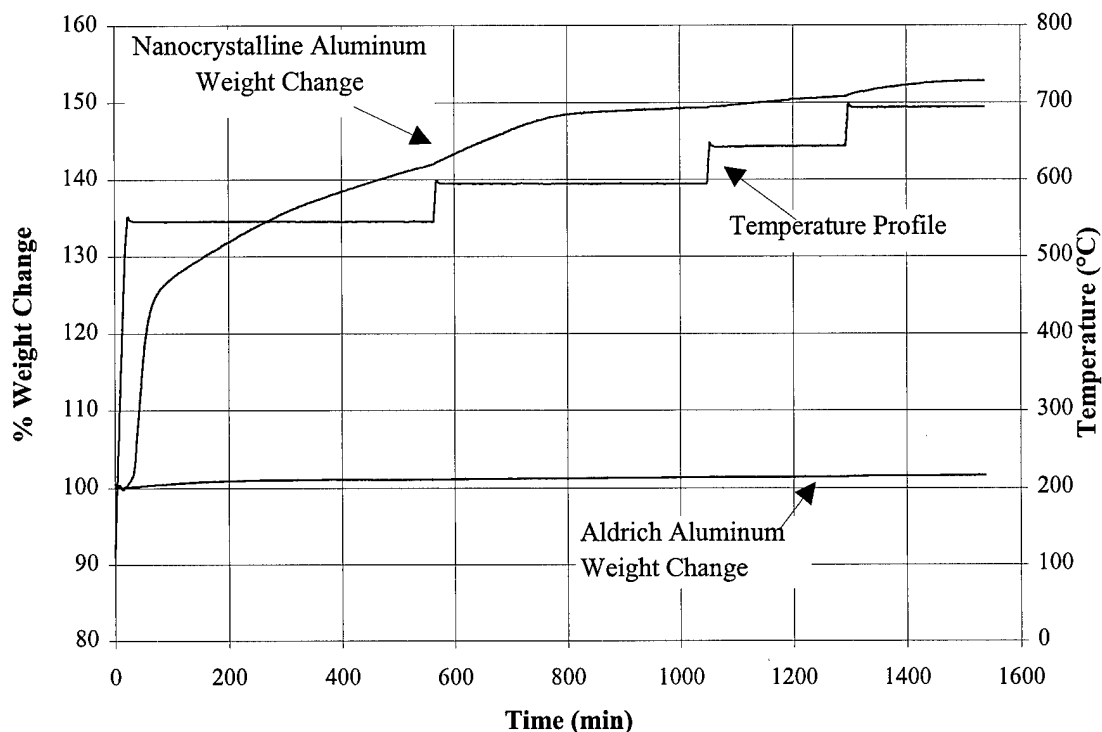
### *Nanocrystalline Aluminum Synthesis and Nitridation*

Recent efforts have been focused on the synthesis and nitridation of nanocrystalline aluminum in order to produce nanocrystalline aluminum nitride via direct nitridation[1]. Typically, temperatures in excess of 1000°C are necessary to complete nitridation of aluminum because of diffusional limitations. The nitridation of large aluminum particles may follow two different paths depending on the temperature of nitridation. The first step is the nitridation of a surface layer that acts as a barrier layer through which the reactants - either aluminum or nitrogen - must diffuse in order to complete the conversion. The next step in the process depends on the temperature of nitridation. Chang *et al.*[2] reported that at temperature below 1200°C the nitrogen diffuses through the AlN layer to react with the aluminum; while at temperatures greater than 1200°C the molten aluminum moves through cracks in the AlN surface and may even result in a hollow particle. The activation energy for the reaction reportedly changed from 1054 kJ/mole to 354 kJ/mole as the temperature was increased above 1200°C. The large increase in the kinetics of nitridation was attributed to the exposure of fresh aluminum surfaces, and a change in the rate limiting step from surface reaction to nitrogen diffusion.

It was initially expected that enhanced nitridation of the nanocrystalline aluminum would be possible and would be due primarily to the decrease in diffusional distances within the aluminum. However, the results obtained (Figure 1) appear to be difficult to explain on this basis alone, though additional quantitative analysis need to be completed. Figure 1 was obtained by nitriding aluminum samples in a Perkin Elmer TGA7 under a 50 cc/min purified grade 5 nitrogen stream. Each sample was purged for 2 hours prior to running the heating cycle in the thermal gravimetric analyzer. Oxygen content in the TGA is still several ppm based upon carbon tests run just prior to the aluminum nitridation. The nanocrystalline aluminum sample created in our forced flow reactor shows significantly more nitridation than does the large 20 µm commercial aluminum spheres. The theoretical nitridation reaction:



should give a weight increase of 151.9%. While the nanocrystalline aluminum produced in our reactor attains approximately this value (153%) during the heat treatment, the commercial aluminum does not achieve any significant weight gain (1.7%). X-ray diffraction patterns of the starting nanocrystalline aluminum and the aluminum nitride created in the TGA are shown in Figure 2. The nanocrystalline aluminum was produced at 7 mbar of pressure and has a grain size of approximately 50 nm.

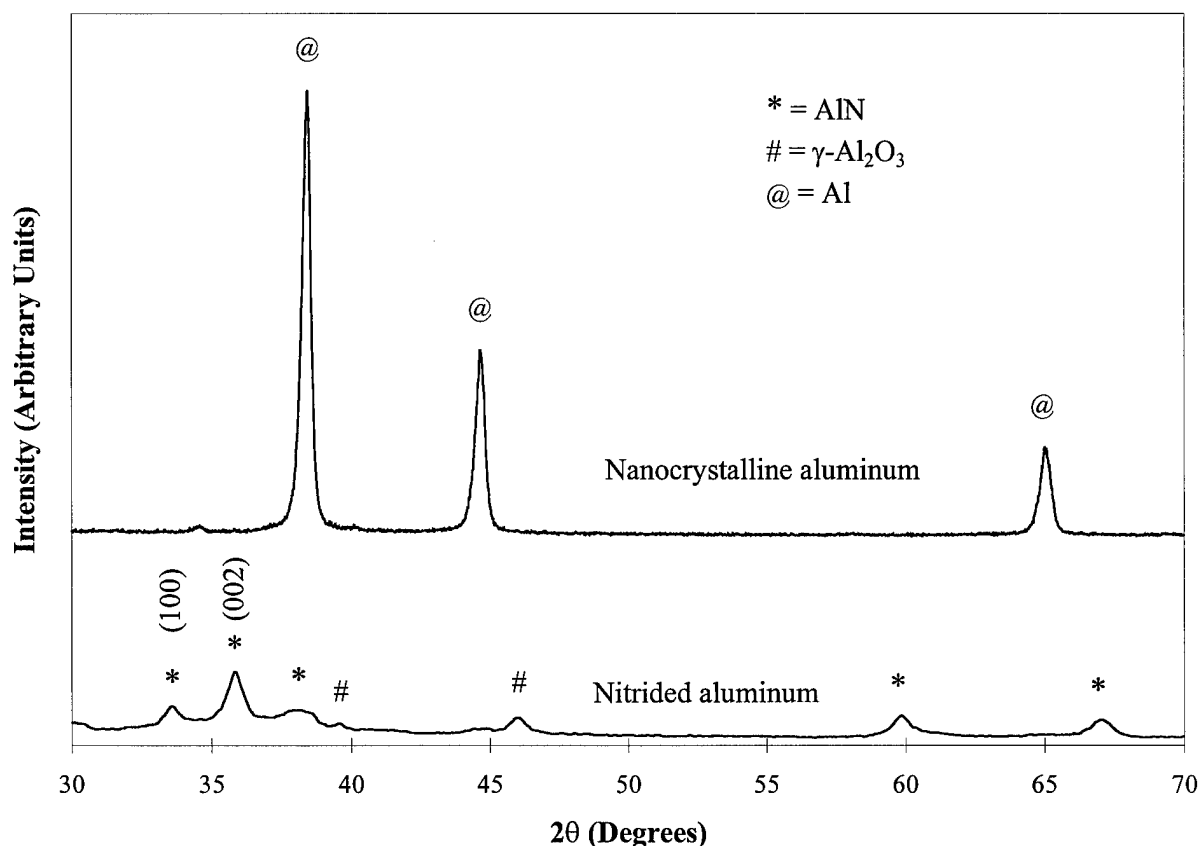


**Figure 1.** Weight change and heating profile for nitridation of nanocrystalline and microcrystalline aluminum.

The nitrated aluminum appears to be made up of three phases, AlN,  $\gamma$ -Al<sub>2</sub>O<sub>3</sub>, and Al, in order of decreasing apparent content. The AlN is the most prevalent component, although it appears to have grown in a nonuniform manner with the (002) reflection having the highest intensity rather than the (100). This has been observed by other researchers, particularly during vapor phase synthesis of AlN, where the grains can be synthesized as large flat hexagonal plates[3]. From the peak broadening in the X-ray diffraction pattern, it appears that nanocrystalline AlN can be synthesized through nitridation of nanocrystalline aluminum. The aluminum content is extremely low, probably less than 5% as estimated from X-ray peak intensities. The  $\gamma$ -Al<sub>2</sub>O<sub>3</sub> is probably formed due to small oxygen leaks in the TGA system. The formation of Al<sub>2</sub>O<sub>3</sub> from Al corresponds to a weight gain of 189% so that partial oxidation of aluminum could result in a fortuitous weight gain. In this case, however, the presence of a large amount of AlN and smaller amounts of  $\gamma$ -Al<sub>2</sub>O<sub>3</sub> and Al as determined by powder X-ray diffraction suggests that the primary source of the weight gain was aluminum nitridation and the  $\gamma$ -Al<sub>2</sub>O<sub>3</sub> is due to small oxygen leaks in the TGA and possibly some crystallization of surface oxides created from exposure to air. Every effort will be made to minimize the oxygen contamination within the TGA, however the sample must be exposed to air during loading into the TGA so some oxygen will always be incorporated into the samples.

The observed low-temperature nitridation of the nanocrystalline materials over the bulk aluminum could be due to two possibilities. The first possibility is that the nanocrystalline aluminum only involves short diffusion distances so that the nitridation kinetics of the smaller particles reach completion significantly sooner than larger particles. The second possibility is that the nanocrystalline aluminum has greater surface reactivity, enabling a higher fraction of nitrogen to readily react with the aluminum. Both of these possibilities will be investigated in detail by nitriding aluminum of different

particle sizes and exposing the aluminum nanoparticles for different periods of time prior to nitridation.



**Figure 2.** Powder X-ray diffraction patterns of nanocrystalline aluminum starting powder and nitrided product.

### ***Future Work***

In order to make large quantities of high-purity nanocrystalline AlN, a quartz nitridation reactor, which can be brought into the glove box for sample loading and unloading, will need to be constructed. This reactor will allow us to treat the material under air-free conditions and will also give us the flexibility to use ammonia to nitride the aluminum. Ammonia offers several advantages including a lower dissociation energy and a purification effect by reacting with any carbon or oxygen impurities to form CH<sub>4</sub> or H<sub>2</sub>O. A more complete analysis of the nitridation kinetics of nanocrystalline aluminum is currently underway, as are experiments to produce pure nanocrystalline AlN directly within the forced flow reactor through the use of nitrogen microwave plasma.

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  - [3] Nickel, K.G., Riedel, R., and Petzow, G., "Thermodynamic and Experimental Study of High-Purity Aluminum Nitride Formation from Aluminum Chloride by Chemical Vapor Deposition" *J. Am. Ceram. Soc.*, **72** [10] 1804-10, (1989).